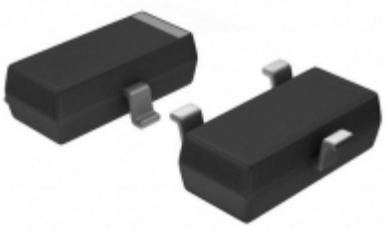
	<h2>SI2323DDS-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI2323DDS-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 5.3A SOT-23</p> <p>Datenblätter:  SI2323DDS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 176205 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2323DDS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 5.3A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	176205 pcs Stock
detaillierte Beschreibung	P-Channel 20V 5.3A (Tc) 960mW (Ta), 1.7W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23
Verlustleistung (max)	960mW (Ta), 1.7W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.3A (Tc)
Rds On (Max) @ Id, Vgs	39 mOhm @ 4.1A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	36nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	1160pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2323DDS-T1-GE3TR

SI2323DDS-T1-GE3 ist neu im Original. Suche SI2323DDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2323DDS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2323DDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2323D SI SI SOT-23</p>	 <p>SI2323DS-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 3.7A SOT23-3</p>	 <p>SI2323DDS-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 5.3A SOT-23</p>	 <p>SI2323DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 3.7A SOT23-3</p>
 <p>SI2323DS VISHAY SI2323DS VISHAY</p>	 <p>SI2323CDS-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 6A SOT-23</p>	 <p>SI2323DDS-T1-E3 Son SI2323DDS-T1-E3 Son</p>	 <p>SI2323DS-T1 Vishay / Siliconix MOSFET P-CH 20V 3.7A SOT23</p>

heiße Teile

Mehr

SI2318DS-T1-GE3	SI2318DS-T1-GE3	SI2319ADS-T1-GE3	SI2319C95TF	SI2319CDS-T1-E3
SI2319CDS-T1-GE3	SI2319CDS-T1-GE3	SI2319DDS-T1-GE3	SI2319DS	SI2319DS-T1-E3
SI2319DS-T1-E3	SI2319DS-T1-GE3	SI2319DS-T1-GE3	SI2320DS	SI2320DS-T1-E3
SI2320DS-T1-GE3	SI2321DS-T1-E3	SI2321DS-T1-E3	SI2321DS-T1-GE3	SI2321DS-T1-GE3
SI2323CDS-T1	SI2323CDS-T1-E3	SI2323CDS-T1-GE3	SI2323CDS-T1-GE3	SI2323DDS-T1-E3
SI2323DDS-T1-GE3	SI2323DS	SI2323DS-T1-E3	SI2323DS-T1-E3	SI2323DS-T1-GE3
SI2323DS-T1-GE3	SI2324DS-T1-E3	SI2324DS-T1-GE3	SI2324DS-T1-GE3	SI2325DS-T1-E3
SI2325DS-T1-E3	SI2325DS-T1-GE3	SI2325DS-T1-GE3	SI2327DS-T1-E3	SI2327DS-T1-E3
SI2327DS-T1-GE3	SI2327DS-T1-GE3	SI2328DS	SI2328DS-T1	SI2328DS-T1-E3
SI2328DS-T1-E3	SI2328DS-T1-GE3	SI2328DS-T1-GE3	SI2329DS-T1-E3	SI2329DS-T1-GE3

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